|   | A 11 41 A1  |   |
|---|---|---|
| •   | Application No.   | Applicant(s)  |
| Aladiaa af Allanaa Lilitaa  | 10/707,709  | LIU ET AL.  |
| Notice of Allowability  | Examiner  | Art Unit  |
|   | Luan Thai   | 2829  |
| The MAILING DATE of this communication app<br>All claims being allowable, PROSECUTION ON THE MERITS I<br>herewith (or previously mailed), a Notice of Allowance (PTOL-8:<br>NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT<br>of the Office or upon petition by the applicant. See 37 CFR 1.3:   | S (OR REMAINS) CLOSED in 5) or other appropriate comminities. This application is a | n this application. If not included unication will be mailed in due course. <b>THIS</b> |
| 1. This communication is responsive to  |   |   |
| 2. The allowed claim(s) is/are 1-20.  |   |   |
| 3. The drawings filed on 06 January 2004 are accepted by  | the Examiner.   |   |
| <ul> <li>4. Acknowledgment is made of a claim for foreign priority a) All b) Some* c) None of the: <ol> <li>Certified copies of the priority documents had</li> <li>Certified copies of the priority documents had</li> <li>Copies of the certified copies of the priority documents had</li> <li>International Bureau (PCT Rule 17.2(a)).</li> </ol> </li> <li>* Certified copies not received:</li> </ul> | ve been received.<br>ve been received in Application                                | on No   |
| Applicant has THREE MONTHS FROM THE "MAILING DATE noted below. Failure to timely comply will result in ABANDON THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.   |   | a reply complying with the requirements   |
| 5. A SUBSTITUTE OATH OR DECLARATION must be sub INFORMAL PATENT APPLICATION (PTO-152) which gi  |   |   |
| <ol> <li>CORRECTED DRAWINGS (as "replacement sheets") medical including changes required by the Notice of Draftsper 1) hereto or 2) to Paper No./Mail Date</li> <li>(b) including changes required by the attached Examine Paper No./Mail Date</li> </ol>   | rson's Patent Drawing Reviev<br>  |   |
| Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in  |   |   |
| 7. DEPOSIT OF and/or INFORMATION about the department attached Examiner's comment regarding REQUIREMENT   |   |   |
| Attachment(s)   |   |   |
| 1. Notice of References Cited (PTO-892)   | 5. Notice of In   | formal Patent Application (PTO-152)   |
| 2. Notice of Draftperson's Patent Drawing Review (PTO-948)  | ·   | ummary (PTO-413),   |
| 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB Paper No./Mail Date 1/6/04   | /08), 7. ☐ Examiner's   | Mail Date Amendment/Comment   |
| <ol> <li>Examiner's Comment Regarding Requirement for Deposit<br/>of Biological Material</li> </ol>   | 9. Other  | Statement of Reasons for Allowance  |
| · PR  | LUANTHAI<br>IMARY EXAMINER  | 9/4/04  |

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04)

## **DETAILED ACTION**

- 1. Claims 1-12 are allowed.
- 2. The following is an examiner's statement of reasons for allowance:

The cited art taken either singly or in combination with other prior arts fails to anticipate or fairly suggest the limitations which the Applicant claims in independent claim 1 in a manner which would warrant a rejection under 35 U.S.C. § 102 or 35 U.S.C. § 103, especially when these limitations are considered within the specific combination claimed.

The cited art, U.S. Pat. No. 6,399,432 to Zheng et al., discloses a process to control poly silicon profiles in a dual doped poly silicon process. Zheng et al., however, fails to anticipate or fairly suggest at least, among other, the method steps of: forming a first locally doped semiconductor region of a first conductivity type and a second locally doped semi-conductor region of a second conductivity type over an undoped, lower semiconductor region; implementing a first etch to simultaneously create a desired pattern in the first and second locally doped semiconductor regions in a manner that also provides a first passivation of exposed sidewalls of the first and second locally doped semiconductor regions, wherein the first etch removes material from the first and second locally doped semiconductor regions at a substantially constant rate with respect to one another, and in a substantially anisotropic manner; and implementing a second etch to complete the desired pattern in the undoped, lower semiconductor region

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in a manner that protects the first and second locally doped semiconductor regions from additional material removal therefrom, as recited in claims 1 and 11.

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3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Luan Thai whose telephone number is 571-272-1935. The examiner can normally be reached on 6:45 AM - 4:15 PM, Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Tokar can be reached on 571-272-1812. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Luan Thai

Primary Examiner Art Unit 2829 September 7, 2004